



STW11NK90Z

N-channel 900V - 0.82Ω - 9.2A - TO-247
Zener-protected SuperMESH™ Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D	P _w
STW11NK90Z	900V	<0.98Ω	9.2A	200W

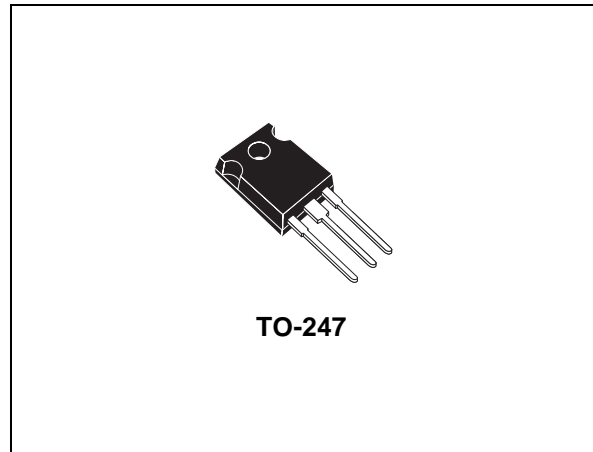
- 100% avalanche tested
- Extremely high dv/dt capability
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeability

Description

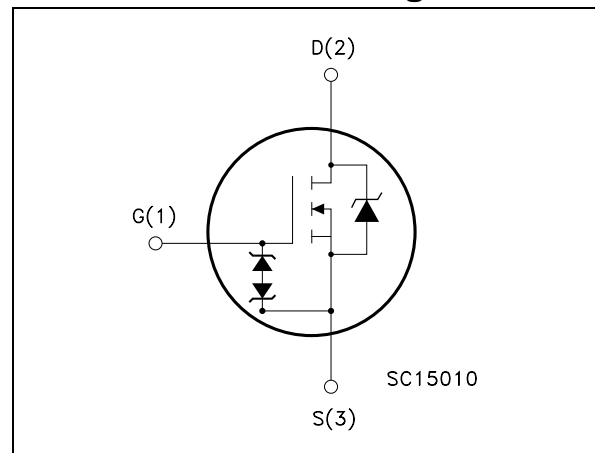
The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage Power MOSFETs including revolutionary MDmesh™ products

Applications

- Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STW11NK90Z	W11NK90Z	TO-247	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	900	V
V_{DGR}	Drain-gate voltage ($R_{GS} = 20K\Omega$)	900	V
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at $T_C = 25^\circ C$	9.2	A
I_D	Drain current (continuous) at $T_C = 100^\circ C$	5.8	A
$I_{DM}^{(1)}$	Drain current (pulsed)	36.8	A
P_{TOT}	Total dissipation at $T_C = 25^\circ C$	200	W
	Derating factor	1.51	W/ $^\circ C$
$V_{ESD(G-D)}$	Gate source ESD(HBM-C=100pF, R=1.5K Ω)	6000	V
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5	V/ns
T_J	Operating junction temperature	-55 to 150	$^\circ C$
T_{stg}	Storage temperature		

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 9.2A$, $di/dt \leq 200A/\mu s$, $V_{DD} = 80\%V_{(BR)DSS}$

Table 2. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case Max	0.66	$^\circ C/W$
R_{thj-a}	Thermal resistance junction-ambient Max	50	$^\circ C/W$
T_l	Maximum lead temperature for soldering purpose	300	$^\circ C$

Table 3. Avalanche data

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J Max)	9.2	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25^\circ C$, $I_d = I_{AR}$, $V_{DD} = 50V$)	400	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1mA, V_{GS} = 0$	900			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating @ } 125^{\circ}C$			1 50	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 100\mu A$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 4.6A$		0.82	0.98	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15V, I_D = 4.6A$		11		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$		3000 240 48		pF pF pF
$C_{oss \text{ eq}}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0V \text{ to } 720V$		83		pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 720V, I_D = 9.2A$ $V_{GS} = 10V$ (see Figure 14)		95 14 49	115	nC nC nC

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2. $C_{oss \text{ eq}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 450V, I_D = 4.6A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see Figure 13)		30 19 76 50		ns ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				9.2	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				36.8	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=9.2A, V_{GS}=0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=9.2A,$ $di/dt = 100A/\mu s,$ $V_{DD}=50V, T_j=25^\circ C$ (see Figure 18)		584 6 21		ns μC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=9.2A,$ $di/dt = 100A/\mu s,$ $V_{DD}=50V, T_j=150^\circ C$ (see Figure 18)		790 8.7 22		ns μC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

Table 8. Gate-source zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$BV_{GSO}^{(1)}$	Gate-source breakdown voltage	$I_{GS}=\pm 1mA$ (open drain)	30			V

1. The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

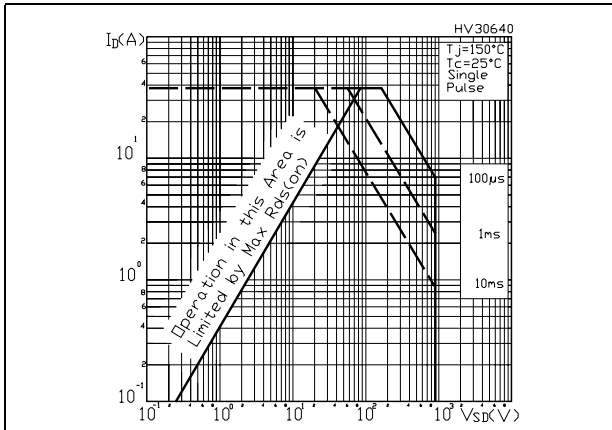


Figure 2. Thermal impedance

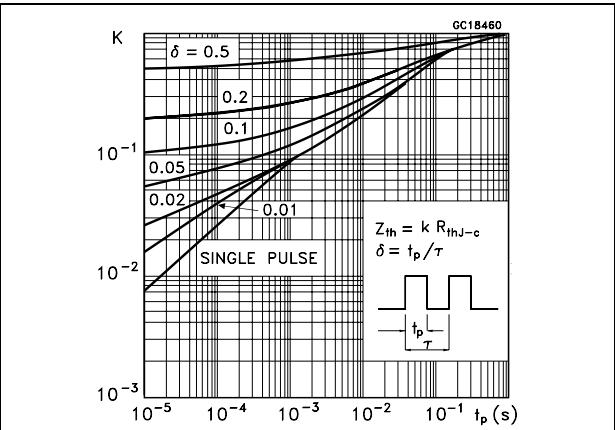


Figure 3. Output characteristics

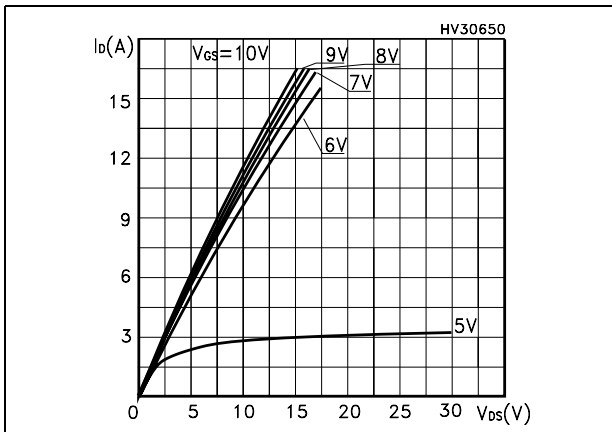


Figure 4. Transfer characteristics

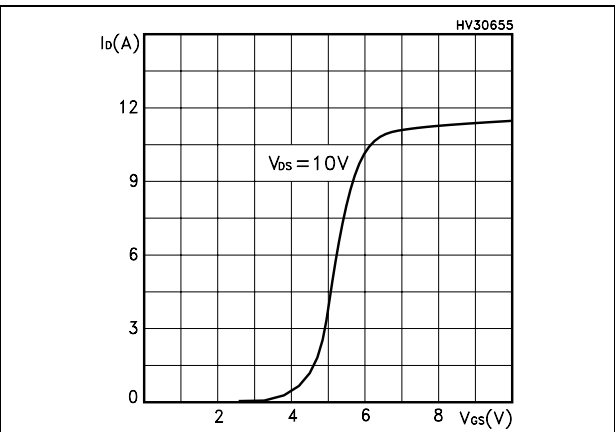


Figure 5. Normalized $B_{V_{DS}}$ vs temperature

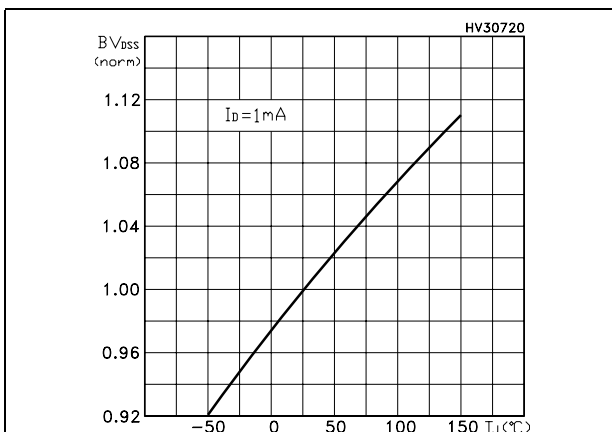


Figure 6. Static drain-source on resistance

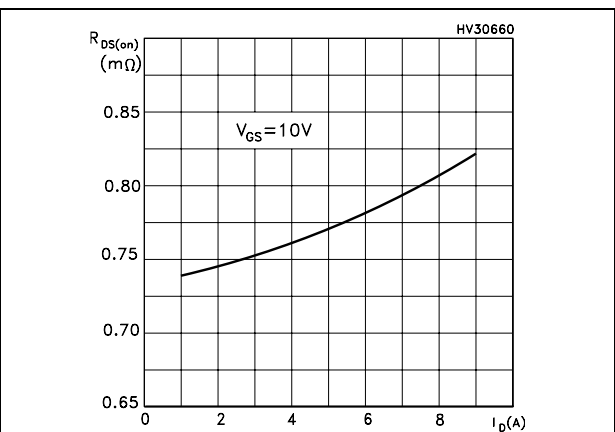


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

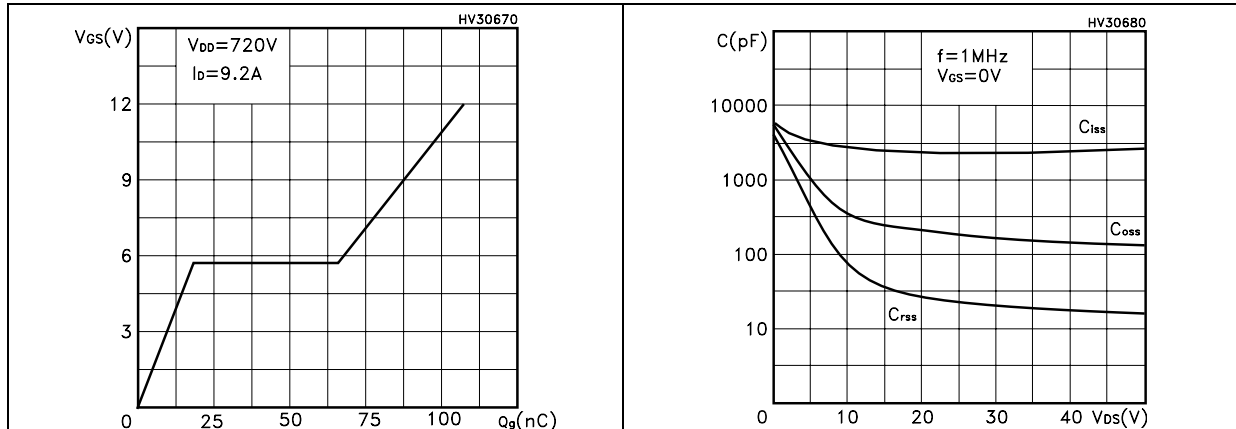


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

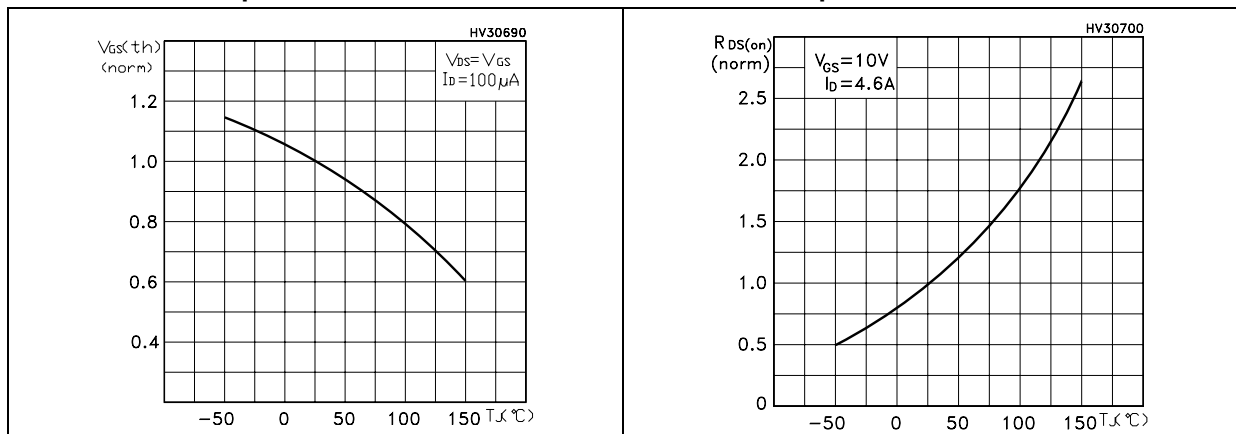
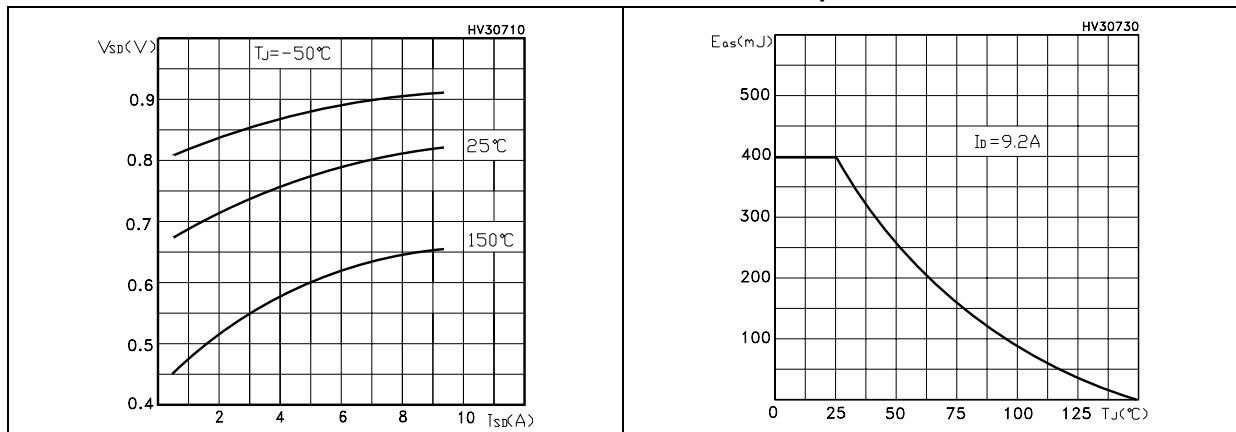


Figure 11. Source-drain diode forward characteristics Figure 12. Maximum avalanche energy vs temperature



3 Test circuits

Figure 13. Switching times test circuit for resistive load

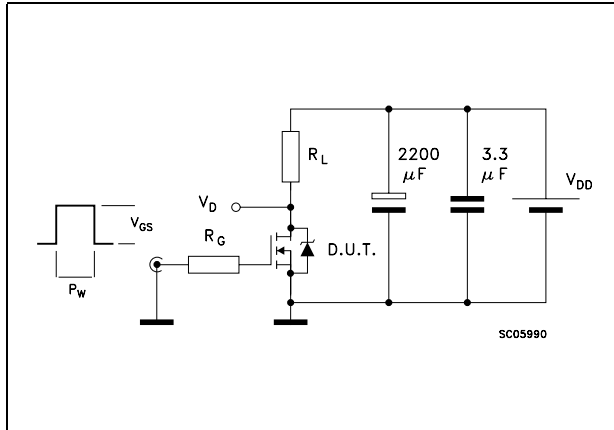


Figure 14. Gate charge test circuit

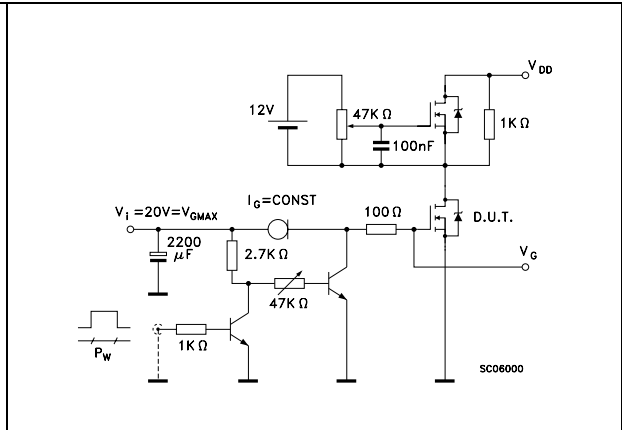


Figure 15. Test circuit for inductive load switching and diode recovery times

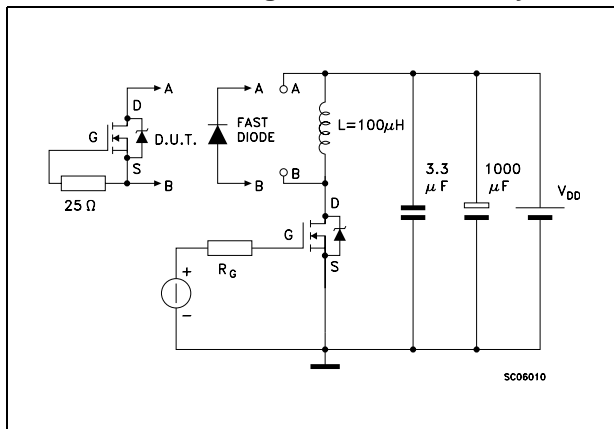


Figure 16. Unclamped Inductive load test circuit

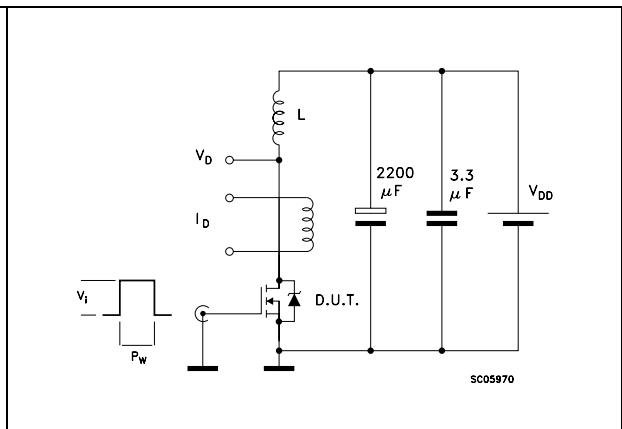


Figure 17. Unclamped inductive waveform

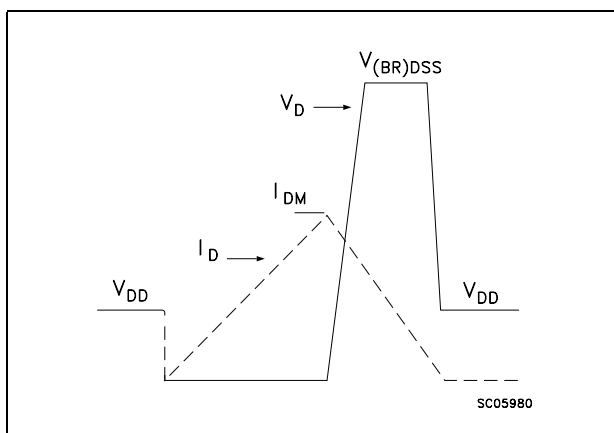
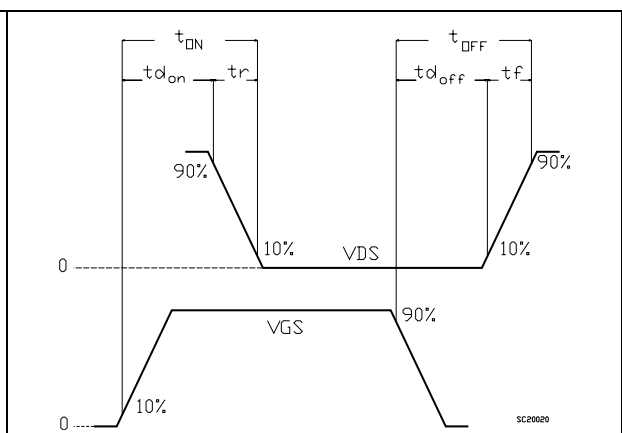


Figure 18. Switching time waveform



TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	

